

## SEMICONDUCTOR TECHNICAL DATA

## KTA1700

EPITAXIAL PLANAR PNP TRANSISTOR

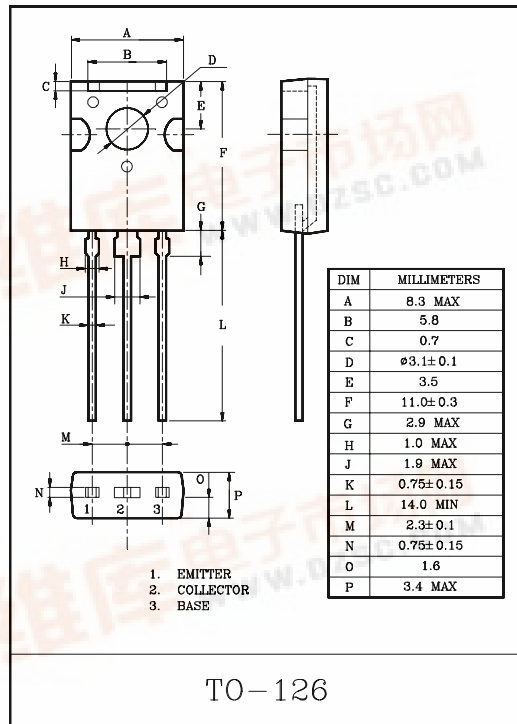
### HIGH VOLTAGE APPLICATION.

### FEATURES

- High Transition Frequency :  $f_T=100\text{MHz(Typ.)}$ .
- Complementary to KTC2800.

### MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		$V_{CBO}$	-160	V
Collector-Emitter Voltage		$V_{CEO}$	-160	V
Emitter-Base Voltage		$V_{EBO}$	-5	V
Collector Current		$I_C$	-1.5	A
Base Current		$I_B$	1.0	A
Collector Power Dissipation	Ta=25°C	$P_C$	1.5	W
	Tc=25°C		10	
Junction Temperature		$T_j$	150	°C
Storage Temperature Range		$T_{stg}$	-55~150	°C



### ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=-160\text{V}, I_E=0$	-	-	-1.0	$\mu\text{A}$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_C=0$	-	-	-1.0	$\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-160	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-5.0	-	-	V
DC Current Gain	$h_{FE}(\text{Note})$	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$	70	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$	-	-	-1.5	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=-5\text{V}, I_C=-500\text{mA}$	-	-	-1.0	V
Transition Frequency	$f_T$	$V_{CE}=-10\text{V}, I_C=-100\text{mA}$	-	100	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$	-	30	-	pF

Note :  $h_{FE}$  Classification 0:70~140, Y:120~240